

RoHS Compliant Product  
A suffix of "-C" specifies halogen & lead-free

## DESCRIPTION

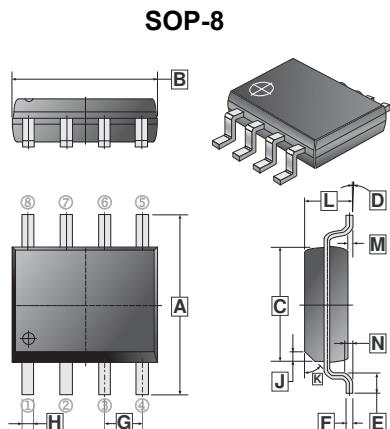
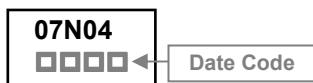
The SSG07N04-C is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

The SSG07N04-C meet the RoHS and Green Product requirement, with full function reliability approved.

## FEATURES

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Green Device Available

## MARKING CODE



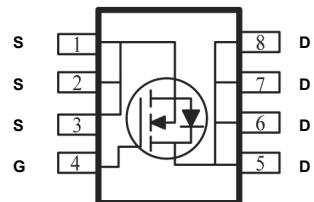
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	5.79	6.20	H	0.33	0.51
B	4.70	5.11	J	0.375	REF.
C	3.80	4.00	K	45°	REF.
D	0°	8°	L	1.3	1.752
E	0.40	1.27	M	0	0.25
F	0.10	0.25	N	0.25	REF.
G	1.27 TYP.				

## PACKAGE INFORMATION

Package	MPQ	Leader Size
SOP-8	2.5K	13' inch

## ORDER INFORMATION

Part Number	Type
SSG07N04-C	Lead (Pb)-free and Halogen-free



## ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings		Unit
Drain-Source Voltage	$V_{DS}$	40		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		V
Continuous Drain Current@ $V_{GS}=10\text{V}^1$	$I_D$	7		A
		5.2		
Pulsed Drain Current <sup>4</sup>	$I_{DM}$	30		A
Power Dissipation <sup>3</sup>	$P_D$	1.5		W
Operating Junction & Storage Temperature Range	$T_J, T_{STG}$	-55~150		°C
Thermal Resistance Ratings				
Thermal Resistance Junction-ambient <sup>1</sup>	$R_{\theta JA}$	85		°C / W
Thermal Resistance Junction-ambient <sup>2</sup>		135		
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	50		

**ELECTRICAL CHARACTERISTICS** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	40	-	-	V	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$
Gate-Threshold Voltage	$\text{V}_{\text{GS(th)}}$	1	-	2.5	V	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$
Forward Transfer conductance	$\text{g}_{\text{fs}}$	-	14	-	S	$\text{V}_{\text{DS}}=5\text{V}, \text{I}_D=5\text{A}$
Gate-Body Leakage	$\text{I}_{\text{GSS}}$	-	-	$\pm 100$	nA	$\text{V}_{\text{GS}}=\pm 20\text{V}$
Zero Gate Voltage Drain Current	$\text{I}_{\text{DSS}}$	-	-	1	$\mu\text{A}$	$\text{V}_{\text{DS}}=32\text{V}, \text{V}_{\text{GS}}=0, T_J=25^\circ\text{C}$
		-	-	5		$\text{V}_{\text{DS}}=32\text{V}, \text{V}_{\text{GS}}=0, T_J=55^\circ\text{C}$
Drain-Source On-Resistance <sup>4</sup>	$\text{R}_{\text{DS(ON)}}$	-	-	30	$\text{m}\Omega$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=6\text{A}$
		-	-	40		$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_D=4\text{A}$
Total Gate Charge	$\text{Q}_g$	-	5.5	-	nC	$\text{I}_D=6\text{A}$ $\text{V}_{\text{DS}}=20\text{V}$ $\text{V}_{\text{GS}}=4.5\text{V}$
Gate-Source Charge	$\text{Q}_{\text{gs}}$	-	1.25	-		
Gate-Drain ("Miller") Charge	$\text{Q}_{\text{gd}}$	-	2.5	-		
Turn-On Delay Time	$\text{T}_{\text{d(on)}}$	-	8.9	-	nS	$\text{V}_{\text{DS}}=20\text{V}$ $\text{I}_D=1\text{A}$ $\text{V}_{\text{GS}}=10\text{V}$ $\text{R}_G=3.3\Omega$
Rise Time	$\text{T}_r$	-	2.2	-		
Turn-Off Delay Time	$\text{T}_{\text{d(off)}}$	-	41	-		
Fall Time	$\text{T}_f$	-	2.7	-		
Input Capacitance	$\text{C}_{\text{iss}}$	-	593	-	pF	$\text{V}_{\text{GS}}=0\text{V}$ $\text{V}_{\text{DS}}=15\text{V}$ $f=1.0\text{MHz}$
Output Capacitance	$\text{C}_{\text{oss}}$	-	76	-		
Reverse Transfer Capacitance	$\text{C}_{\text{rss}}$	-	56	-		
<b>Source-Drain Diode</b>						
Forward On Voltage <sup>4</sup>	$\text{V}_{\text{SD}}$	-	-	1.2	V	$\text{I}_S=1\text{A}, \text{V}_{\text{GS}}=0\text{V}$
Continuous Source Current <sup>1</sup>	$\text{I}_S$	-	-	7	A	
Pulsed Source Current <sup>3 4</sup>	$\text{I}_{\text{SM}}$	-	-	30	A	

Notes:

1. Surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
2. When mounted on Min. copper pad.
3. The power dissipation is limited by 150°C junction temperature.
4. The data tested by pulsed, pulse width  $\leq 300\text{us}$ , duty cycle  $\leq 2\%$

## CHARACTERISTICS CURVE

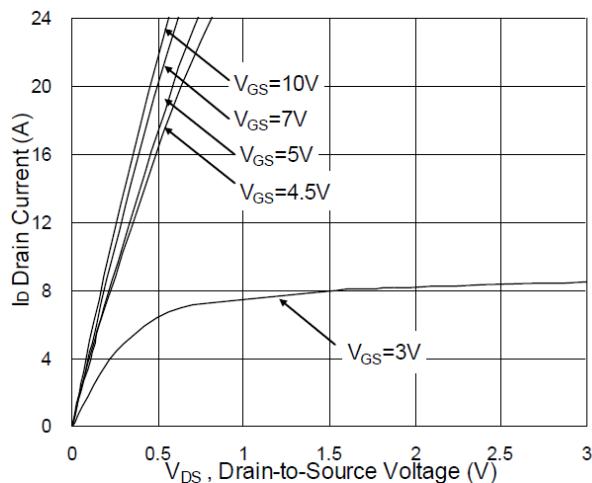


Fig.1 Typical Output Characteristics

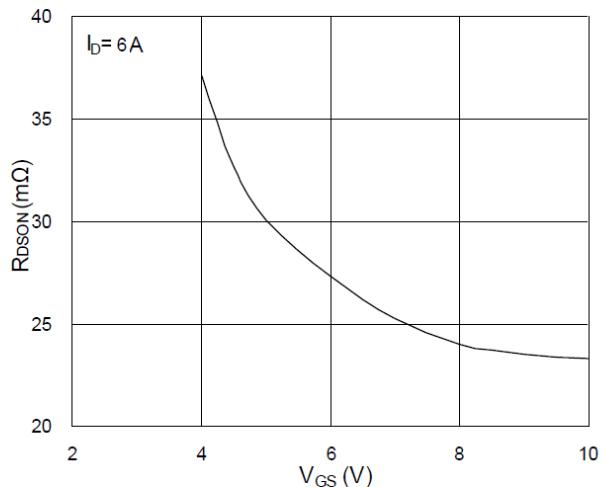


Fig.2 On-Resistance vs. G-S Voltage

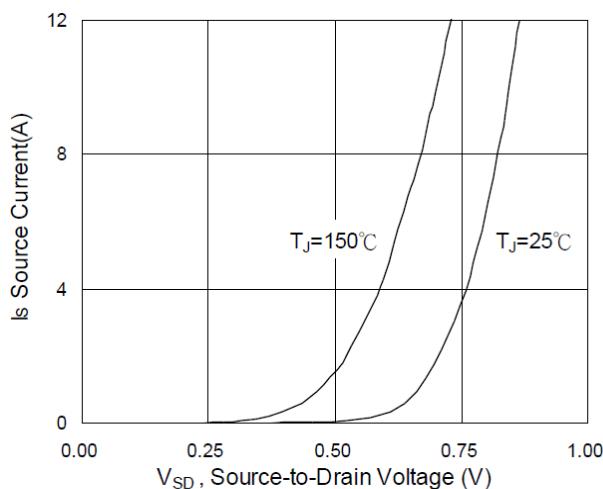


Fig.3 Forward Characteristics of Reverse

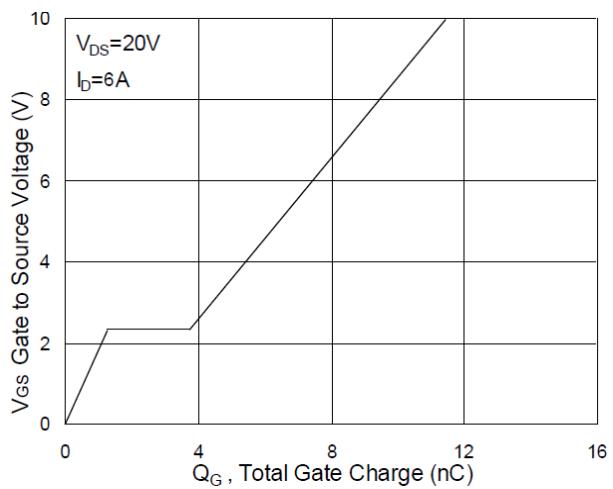


Fig.4 Gate-Charge Characteristics

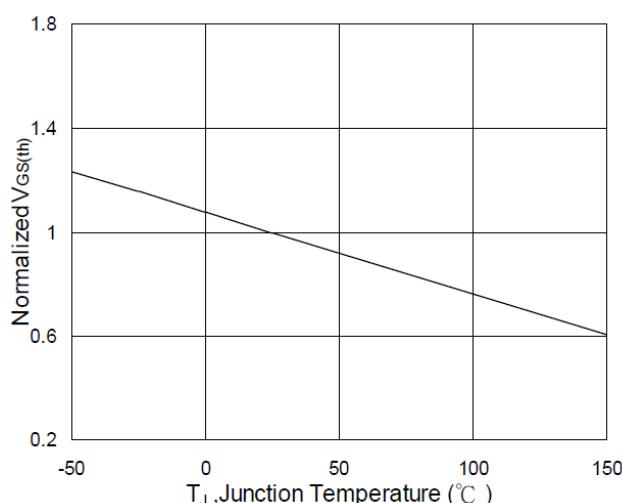


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

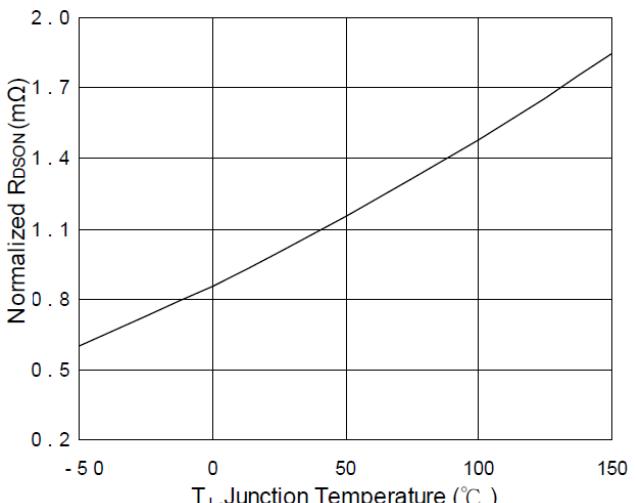


Fig.6 Normalized  $R_{DS(ON)}$  vs.  $T_J$

## CHARACTERISTICS CURVE

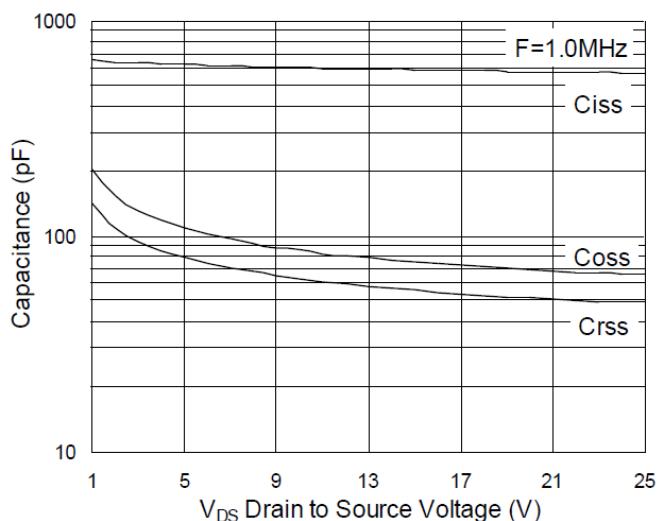


Fig.7 Capacitance

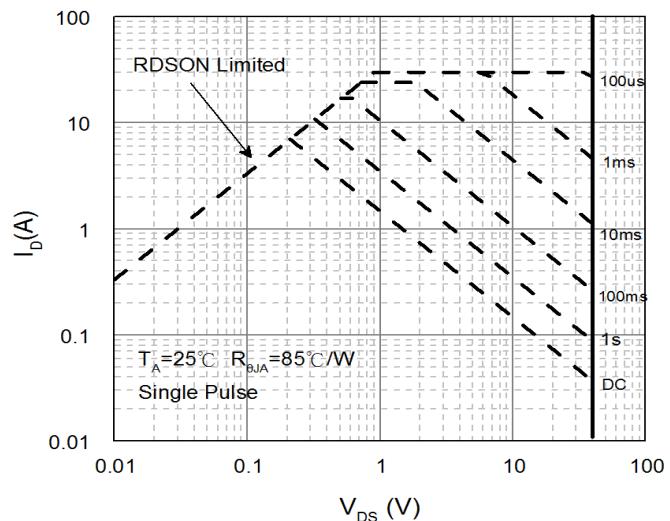


Fig.8 Safe Operating Area

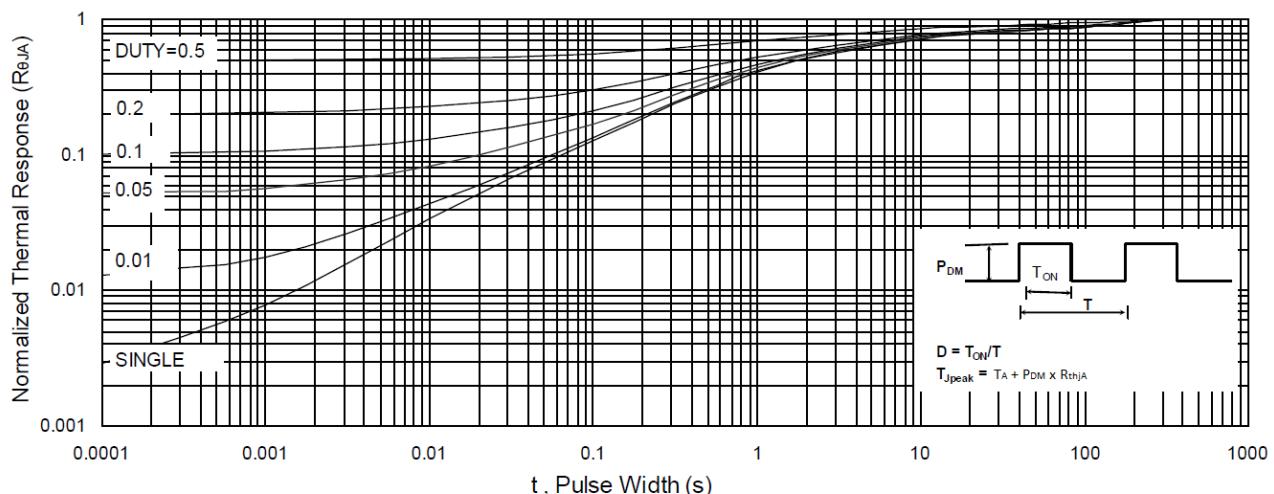


Fig.9 Normalized Maximum Transient Thermal Impedance

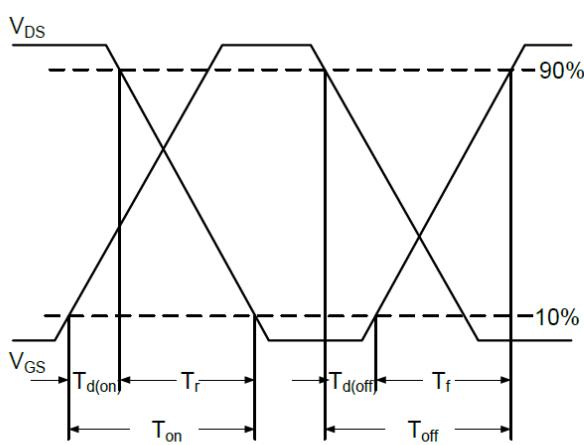


Fig.10 Switching Time Waveform

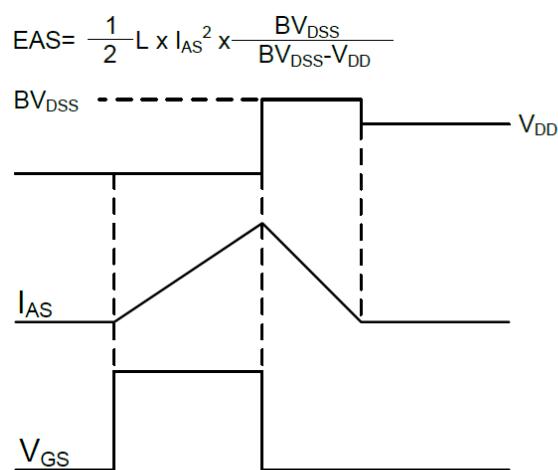


Fig.11 Unclamped Inductive Switching Waveform